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Method to manufacture Indium Nitride quantum dots.

Abstract of the disclosure

The invention concerns a method for manufacturing sizeable quantum dots of Indium Nitride in which a layer of Indium Nitride is grown onto a layer of crystalline buffer. The crystalline buffer is chosen with a lattice structure similar to the lattice structure of Indium Nitride and with the lattice mismatch between Indium Nitride and the crystalline buffer being greater than 5%. During the growth of Indium Nitride, surface strains are produced by the crystalline buffer, allowing the Indium Nitride to self-organise onto the crystalline buffer so as to form a plurality of sizeable quantum dots.